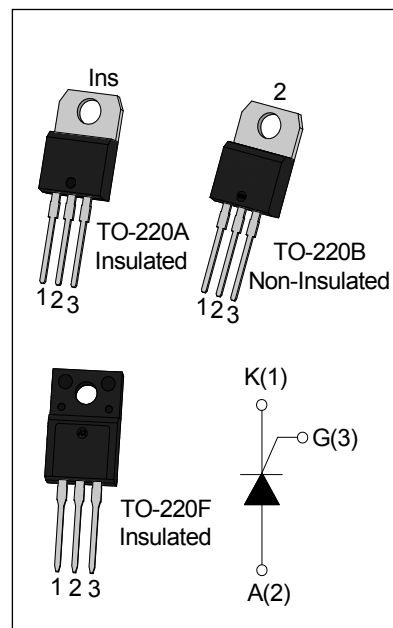




### DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1625 SCRs provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.

From all three terminals to external heatsink, JCT1625A provides a rated insulation voltage of 2500 V<sub>RMS</sub>, and JCT1625F provides a rated insulation voltage of 2000 V<sub>RMS</sub>, complying with UL standards (File ref: E252906). All the packages Listed above are RoHS compliant. (2011/65/EU)



### MAIN FEATURES

Symbol	JCT1625
V <sub>DRM</sub> / V <sub>RPM</sub>	1600V
I <sub>T(RMS)</sub>	25A
I <sub>GT</sub>	≤35mA

### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T <sub>stg</sub>	-40-150	°C
Operating junction temperature range	T <sub>j</sub>	-40-125	°C
Repetitive peak off-state voltage(T <sub>j</sub> =25°C)	V <sub>DRM</sub>	1600	V
Repetitive peak reverse voltage(T <sub>j</sub> =25°C)	V <sub>RPM</sub>	1600	V
RMS on-state current	TO-220A(Ins) / TO-220F(Ins) (T <sub>c</sub> =70°C)	25	A
	TO-220B(Non-Ins) (T <sub>c</sub> =85°C)		
Non repetitive surge peak on-state current (tp=10ms)	I <sub>TSM</sub>	250	A

I <sup>2</sup> t value for fusing (tp=10ms)	I <sup>2</sup> t	310	A <sup>2</sup> s
Critical rate of rise of on-state current (I <sub>G</sub> =2×I <sub>GT</sub> )	dI/dt	100	A/μs
Peak gate current	I <sub>GM</sub>	1.5	A
Average gate power dissipation	P <sub>G(AV)</sub>	2	W
Peak gate power	P <sub>GM</sub>	5	W

**ELECTRICAL CHARACTERISTICS** (T<sub>j</sub>=25°C unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	-	-	35	mA
V <sub>GT</sub>		-	-	1.5	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ	0.25	-	-	V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	-	-	150	mA
I <sub>H</sub>	I <sub>T</sub> =500mA	-	-	120	mA
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125°C	1000	-	-	V/μs

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
V <sub>TM</sub>	I <sub>TM</sub> =50A tp=380μs	T <sub>j</sub> =25°C	1.8	V
I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =25°C	10	μA
I <sub>RRM</sub>		T <sub>j</sub> =125°C	4	mA

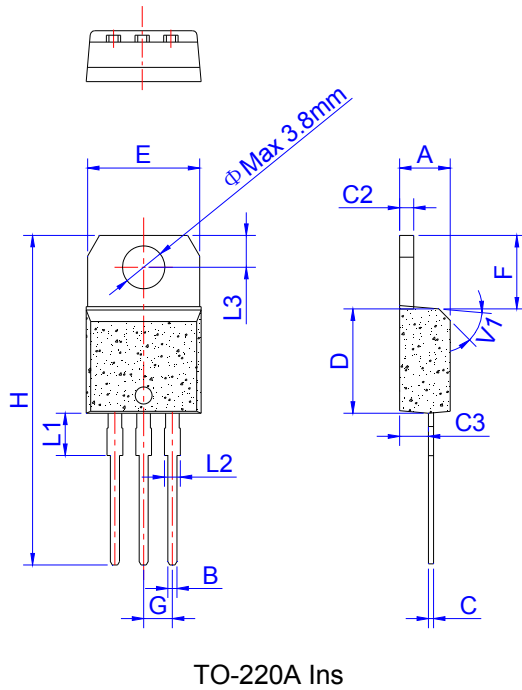
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	junction to case(AC)	TO-220A(Ins)	2.1	°C/W
		TO-220B(Non-Ins)	1.1	
		TO-220F(Ins)	2.3	

ORDERING INFORMATION

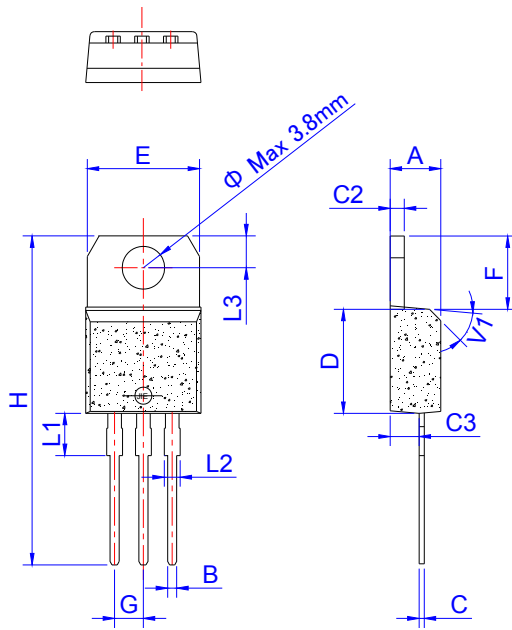
JieJie Microelectronics Co.,Ltd	J	CT	16	25	B
		SCRs		$I_{T(RMS)}:25A$	A:TO-220A(Ins) F:TO-220F(Ins) B:TO-220B(Non-Ins)
			16: $V_{DRM} / V_{RRM} \geq 1600V$		

PACKAGE MECHANICAL DATA



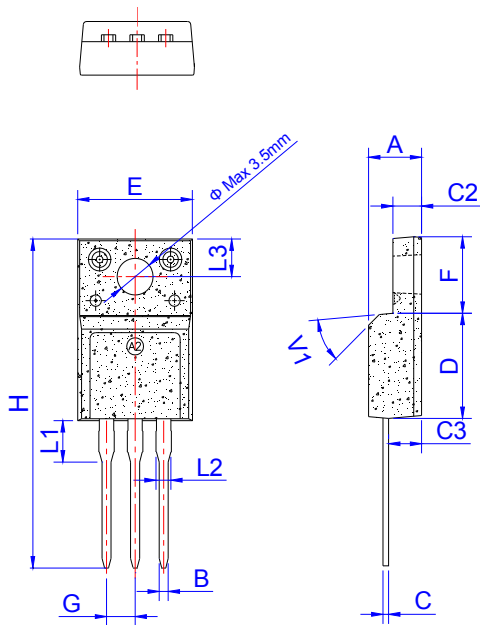
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA



TO-220B Non-Ins

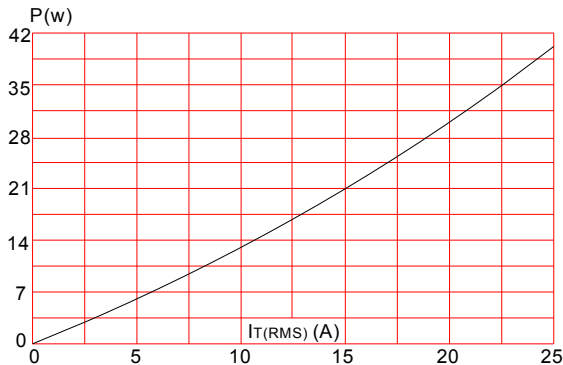
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



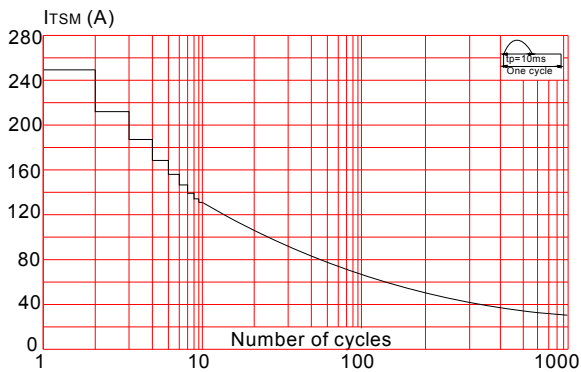
TO-220F Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

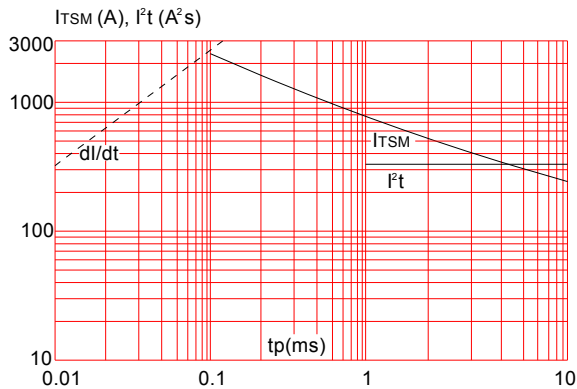
**FIG.1** Maximum power dissipation versus RMS on-state current



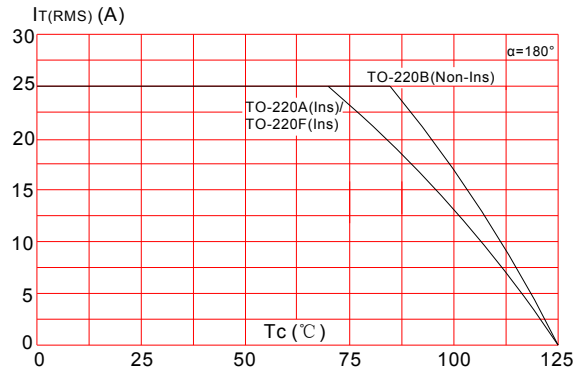
**FIG.3:** Surge peak on-state current versus number of cycles



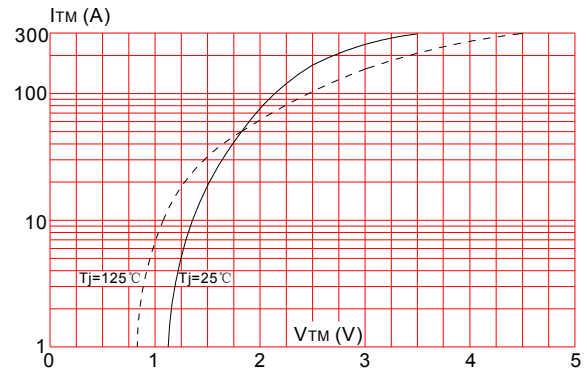
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 100\text{A}/\mu\text{s}$ )



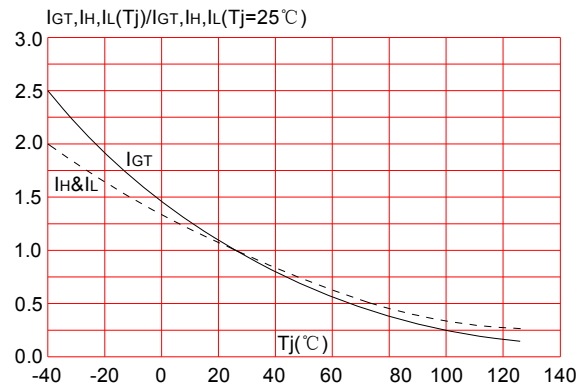
**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature




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